

Surface-mount MOS FET Array SDK08

Absolute Maximum Ratings (Ta=25°C)

Symbol	Ratings	Unit
V _{DSS}	50	V
V _{GSS}	±20	V
I _D	±4.5	A
I _D (pulse) *1	±9	A
P _T	4 (Tc=25°C, 4 circuits operate)	W
EAS *2	80	mJ
T _{ch}	150	°C
T _{stg}	-55 to +150	°C

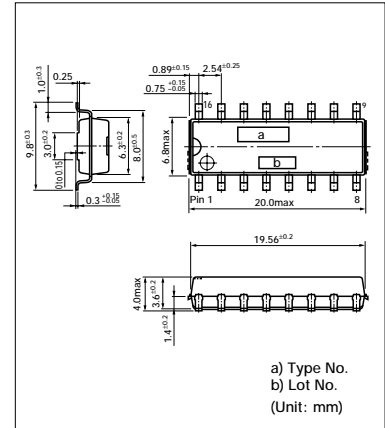
*1 P_W ≤ 100μs, duty ≤ 1%

*2 V_{DD} = 12V, L = 10mH, unclamped, R_G = 50Ω

Electrical Characteristics (Ta=25°C)

Symbol	Test Conditions	Ratings			Unit
		min	typ	max	
V _{(BR) DSS}	I _D = 100μA, V _{GS} = 0V	50			V
I _{GSS}	V _{GS} = ±20V			±100	nA
I _{DSS}	V _{DS} = 50V, V _{GS} = 0V			100	μA
V _{TH}	V _{DS} = 10V, I _D = 1mA	1.3	1.8	2.3	V
Re (yfs)	V _{DS} = 10V, I _D = 4.0A	5.0	9.0	13.0	S
R _{DS (ON)}	V _{GS} = 10V, I _D = 4.0A		0.07	0.08	Ω
	V _{GS} = 4V, I _D = 4.0A		0.09	0.1	Ω
C _{iss}	V _{DS} = 10V		700		pF
C _{oss}	f = 1.0MHz		300		pF
C _{rss}	V _{GS} = 0V		90		pF
t _{d (on)}	I _D = 4A		50		ns
t _r	V _{DD} ≈ 12V		80		ns
t _{d (off)}	R _L = 3Ω		60		ns
t _f	V _{GS} = 5V		40		ns
V _{SD}	I _{SD} = 6A, V _{GS} = 0V		1.0	1.5	V

External Dimensions SMD-16A



Equivalent Circuit Diagram

